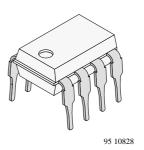


Dual Channel Optocoupler with Phototransistor Output

Description

The MCT6 and MCT62 consists of a phototransistor optically coupled to a gallium arsenide infrared-emitting diode in a 6-lead plastic dual inline package.

The elements are mounted on one leadframe using a coplanar technique, providing a fixed distance between input and output for highest safety requirements.





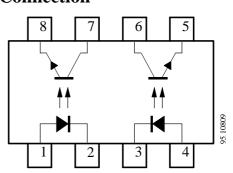
Applications

Galvanically separated circuits, non-interacting switches

Features

- Current Transfer Ratio (CTR) of typical 100%
- DC isolation test voltage $V_{IO} = 2.5 \text{ kV}$
- Low temperature coefficient of CTR
- Low coupling capacitance of typical 0.3 pF
- Wide ambient temperature range
- UL recognized; file No. E 76222

Pin Connection



MCT6/MCT62



Absolute Maximum Ratings

Input (Emitter)

Parameters	Test Conditions	Symbol	Value	Unit
Reserve voltage		V_R	6	V
Forward current		I_{F}	60	mA
Forward surge current	$t_p \le 10 \ \mu s$	I _{FSM}	1.5	A
Power dissipation	$T_{amb} \le 25^{\circ}C$	P_{V}	100	mW
Junction temperature		T _i	125	°C

Output (Detector)

Parameters	Test Conditions	Symbol	Value	Unit
Collector emitter voltage		V _{CEO}	70	V
Emitter collector voltage		V _{ECO}	7	V
Collector current		I _C	50	mA
Collector peak current	$t_p/T = 0.5, t_p \le 10 \text{ ms}$	I _{CM}	100	mA
Power dissipation	$T_{amb} \le 25^{\circ}C$	P _v	150	mW
Junction temperature		T _j	125	°C

Coupler

Parameters	Test Conditions		Symbol	Value	Unit
DC isolation test voltage			$V_{IO}^{1)}$	2.5	kV
Total power dissipation	$T_{amb} \le 25$ °C P_{tot}		P _{tot}	250	mW
Ambient temperature range			T _{amb}	-40 to +100	°C
Storage temperature range			T _{stg}	-55 to +125	°C
Soldering temperature	2 mm from case, t:	≤ 10 s	T_{sd}	260	°C

1) Related to standard climate 23/50 DIN 50 014



Electrical Characteristics

For single coupled system, $T_{amb} = 25^{\circ}C$

Input (Emitter)

Parameters	Test Conditions	Symbol	Min.	Тур.	Max.	Unit
Forward voltage	$I_F = 50 \text{ mA}$	V_{F}		1.25	1.6	V
Breakdown voltage	$I_R = 100 \mu A$	V _(BR)	5			V

Output (Detector)

Parameters	Test Conditions	Symbol	Min.	Typ.	Max.	Unit
Collector emitter breakdown voltage	$I_C = 1 \text{ mA}$	V _{(BR)CEO}	70			V
Emitter collector breakdown voltage	$I_E = 100 \mu A$	V _{(BR)ECO}	7			V
Collector dark current	$V_{CE} = 20 \text{ V},$ $I_F = 0, E = 0$	I _{CEO}			100	nA

Coupler

Parameters	Test Conditions	Symbol	Min.	Тур.	Max.	Unit
DC isolation test voltage	t = 2 s	V _{IO} 1)	2.5			kV
Isolation resistance	$V_{IO} = 1000 \text{ V},$ 40% relative humidity	R _{IO} 1)		10^{12}		Ω
Collector emitter saturation voltage	$I_F = 10 \text{ mA}, I_C = 1 \text{ mA}$	V _{CEsat}			0.3	V
Cut-off frequency	$I_F = 10 \text{ mA}, V_{CE} = 5 \text{ V},$ $R_L = 100 \Omega$	f_{C}		100		kHz
Coupling capacitance	f = 1 MHz	C_k		0.3		pF

¹⁾ Related to standard climate 23/50 DIN 50 014

Current Transfer Ratio (CTR)

Parameters	Test Conditions	Type	Symbol	Min.	Typ.	Max.	Unit
$I_{\rm C}/I_{\rm F}$	$V_{CE} = 5 \text{ V}, I_F = 5 \text{ mA}$	MCT6	CTR	0.5	1		
$I_{\rm C}/I_{\rm F}$	$V_{CE} = 5 \text{ V}, I_F = 10 \text{ mA}$	MCT6	CTR	0.6	1.2		
$I_{\rm C}/I_{\rm F}$	$V_{CE} = 5 \text{ V}, I_F = 5 \text{ mA}$	MCT62	CTR	1	2		



Switching Characteristics (Typical Values)

 $V_S = 5 V$

T	$R_L = 100 \Omega$ (see figure 1)							
Туре		t _r [µs]	ton[µs]	t _s [μs]	t _f [µs]	t _{off} [µs]	I _C [mA]	
MCT6/ MCT62		3.0	6.0	0.3	4.7	5.0	2.0	

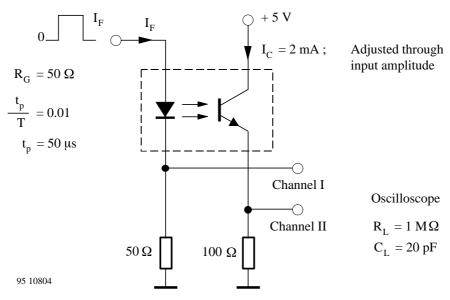


Figure 1. Test circuit

Typical Characteristics ($T_{amb} = 25$ °C, unless otherwise specified)

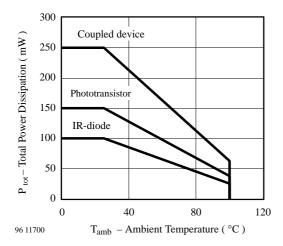


Figure 2. Total Power Dissipation vs. Ambient Temperature

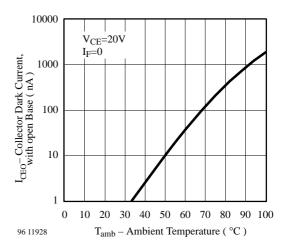


Figure 5. Collector Dark Current vs. Ambient Temperature

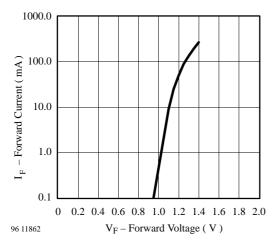


Figure 3. Forward Current vs. Forward Voltage

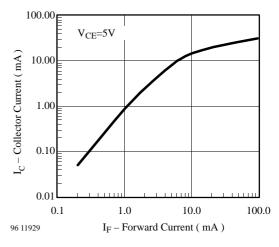


Figure 6. Collector Current vs. Forward Current

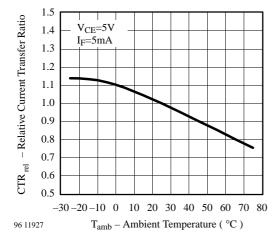


Figure 4. Rel. Current Transfer Ratio vs. Ambient Temperature

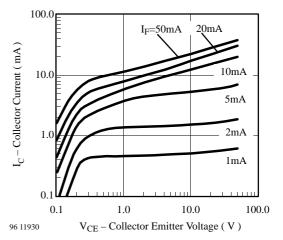
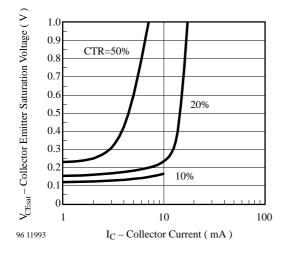


Figure 7. Collector Current vs. Collector Emitter Voltage



Typical Characteristics ($T_{amb} = 25$ °C, unless otherwise specified)



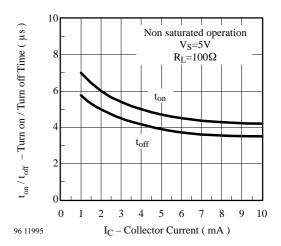


Figure 8. Collector Emitter Sat. Voltage vs. Collector Current

Figure 10. Turn on / off Time vs. Collector Current

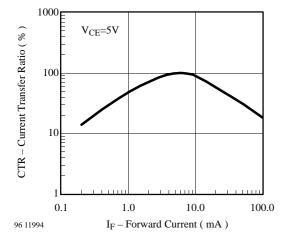
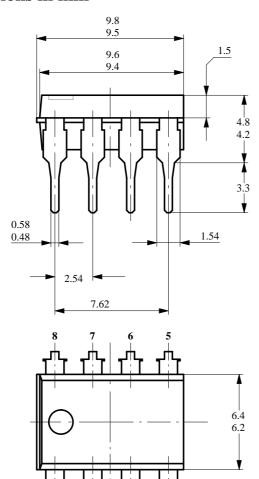
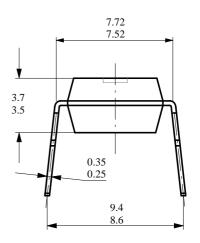


Figure 9. Current Transfer Ratio vs. Forward Current



Dimensions in mm





95 10949



MCT6/MCT62



Ozone Depleting Substances Policy Statement

It is the policy of TEMIC TELEFUNKEN microelectronic GmbH to

- 1. Meet all present and future national and international statutory requirements.
- 2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

TEMIC TELEFUNKEN microelectronic GmbH semiconductor division has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

- 1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
- 2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
- 3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

TEMIC can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

We reserve the right to make changes to improve technical design and may do so without further notice.

Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer. Should the buyer use TEMIC products for any unintended or unauthorized application, the buyer shall indemnify TEMIC against all claims, costs, damages, and expenses, arising out of, directly or indirectly, any claim of personal damage, injury or death associated with such unintended or unauthorized use.

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